# Regarding the change of names mentioned in the document, such as Mitsubishi Electric and Mitsubishi XX, to Renesas Technology Corp.

The semiconductor operations of Hitachi and Mitsubishi Electric were transferred to Renesas Technology Corporation on April 1st 2003. These operations include microcomputer, logic, analog and discrete devices, and memory chips other than DRAMs (flash memory, SRAMs etc.) Accordingly, although Mitsubishi Electric, Mitsubishi Electric Corporation, Mitsubishi Semiconductors, and other Mitsubishi brand names are mentioned in the document, these names have in fact all been changed to Renesas Technology Corp. Thank you for your understanding. Except for our corporate trademark, logo and corporate statement, no changes whatsoever have been made to the contents of the document, and these changes do not constitute any alteration to the contents of the document itself.

Note: Mitsubishi Electric will continue the business operations of high frequency & optical devices and power devices.

Renesas Technology Corp. Customer Support Dept. April 1, 2003



# M66312P/FP

# 8-BIT LED DRIVER WITH SHIFTREGISTER AND LATCHED 3-STATE OUTPUTS

#### DESCRIPTION

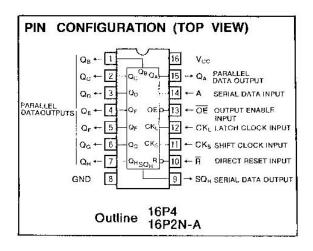
M66312 is a LED array driver having a 8-bit serial input and parallel output shiftregister function with 3-state output latch

This product guarantees the output electric current of 16mA which is sufficient for LED drive, capable of flowing 8 bits continuously at the same time, and use either of cathode common LED and anode common LED.

In addition, as this product has been designed in complete CMOS, power consumption can be greatly reduced when compared with conventional BIPOLAR or Bi-CMOS products.

#### **FEATURES**

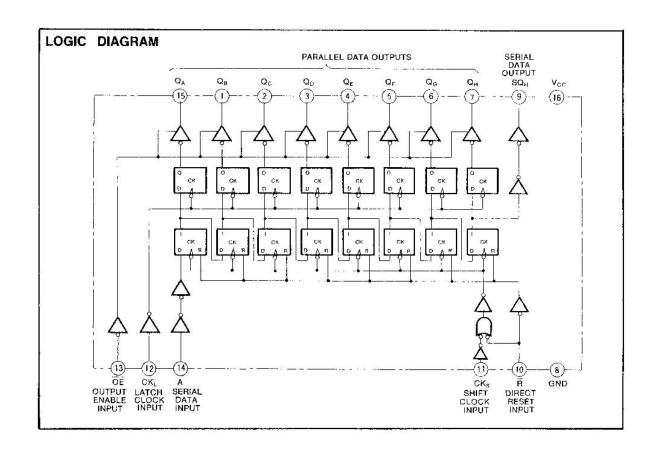
- High output current l<sub>OL</sub>=16mA, l<sub>OH</sub>=−16mA
- High speed (clock freguency): 30MHz (typ)
  (C<sub>L</sub>=50<sub>p</sub>F, V<sub>CC</sub>=5V)
- Low power dissipation : 20µW/package (max)
  (V<sub>CC</sub>=5V, Ta=25℃, quiescent state)
- 3-state output (except serial data output)
- Wide operating temperature range : Ta=-40~+85℃



#### **APPLICATION**

LED array drive of PRINTER

LED array drive of BUTTON TELEPHONE





#### **FUNCTIONAL DESCRIPTION**

As M66312 uses silicon gate CMOS process, it realizes high-speed and high-output currents sufficient for LED drive while maintaining low power consumption and altowance for high noises.

Each bit of a shiftregister consists of two flip-flops having independent clocks for shifting and latching.

As for clock input, shift clock input  $CK_S$  and latch clock input  $CK_L$  are independent from each other, shift and latch operations being made when "L" changes to "H".

Serial data input A is the data input of the first-step shiftregister and the signal of A shifts shifting registers one by one when a pulse is impressed to CK<sub>5</sub>. When A is "H", the signal of "H" shifts. When A is "L", the signal of "L" shifts.

When the pulse is impressed to CKL, the contents of the

shifting register at that time are stored in a latching register, and they appear in the output from  $Q_A$  through  $Q_H$  are 3-state outputs.

To extend the number of bits, serial data output  $SQ_H$  is used to output the 8-bit of the shift register.

By connecting CKs and CKL, the shift register state delayed by 1 clock cycle is output at  $\mathbf{Q}_A$  through  $\mathbf{Q}_H$ .

When reset input  $\overline{R}$  is low, shift register and  $SQ_H$  will be reset. To reset  $Q_A$  through  $Q_H$  to low-level,  $CK_L$  must be changed from low-level to high-level after the shift register is reset by  $\overline{R}$ .

When output-enable input  $\overline{OE}$  is high,  $Q_A$  through  $Q_H$  will become high impedance state, but  $SQ_H$  is not changed. Even if  $\overline{OE}$  is changed, shift operation is not affected.

### FUNCTION TABLE (Note: 1)

Operation mode		Input				Parallet data output							Serial data		
— Operation	on mode	F	CKs	CKt	Α	ŌE	QA	Св	Q <sub>C</sub>	. Q <sub>D</sub>	QE	QF	Qc	Qij	output SQ <sub>H</sub>
Reset	Shift t <sub>1</sub>	L	X	Х	X	L	Q <sub>A</sub> G	Q <sub>0</sub> 0	Q <sub>c</sub> o	Q <sub>0</sub> °	Q <sub>E</sub> <sup>0</sup>	O <sub>F</sub>	Q <sub>o</sub> o	Q <sub>H</sub> <sup>0</sup>	L
116361	Latch t <sub>2</sub>	Х	X	1	Х	L	, ц	L	L	L	L	L	L	L	L
Shift	Shift t <sub>1</sub>	Н	1	Х	н	L	O <sub>A</sub> n	Q <sub>B</sub> °	Q <sub>C</sub> °	Q <sub>p</sub> n	Q <sub>E</sub> <sup>0</sup>	O <sub>F</sub> <sup>O</sup>	Qg <sup>0</sup>	Q <sub>H</sub> <sup>0</sup>	q <sub>G</sub> <sup>D</sup>
latch	Latch t <sub>2</sub>	Н	X	1	X	L	н	q <sub>A</sub> <sup>U</sup>	d <sub>B</sub> o	q <sub>o</sub> o	q <sub>D</sub> <sup>0</sup>	q <sub>e</sub> o	Qe <sup>0</sup>	q <sub>G</sub> <sup>0</sup>	q <sub>G</sub> <sup>a</sup>
operation	Shift t <sub>1</sub>	Н	1	×	L	L,	O <sub>A</sub> 0	Q <sub>B</sub> <sup>0</sup>	Q <sub>C</sub> <sup>0</sup>	Op <sup>0</sup>	Q <sub>E</sub> <sup>0</sup>	Q <sub>e</sub> 0	Q <sub>0</sub>	Q <sub>H</sub> °	qe°
орегация	Latch t <sub>2</sub>	Н	Х	1	Х	L	L	GA <sup>O</sup>	qs	9c°	qo°	q <sub>E</sub> <sup>0</sup>	d <sup>e</sup> 0	qg <sup>a</sup>	de <sub>o</sub>
3 st	ate	X	X	Х	X	Н	Z	Z	Z	Z	Z	Z	Z	Z	 <b>Q</b> н

Note 1 : † : Change from low-level to high-level

Q<sup>0</sup> : Output state Q before CK<sub>L</sub> changed

X : Irrelevan

qu : Contents of shift register before CKs changed

q : Contents of shift register

t<sub>1</sub>, t<sub>2</sub> : t<sub>2</sub> is set after t<sub>1</sub> is set Z : High impedance



### ABSOLUTE MAXIMUM RATINGS (Ta=-40~+85°C, unless otherwise noted)

Symbol	Parameter		Conditions	Ratings	Unit		
Voc	Supply voltage	unar establi	W. W	0.5~   7.0	٧		
Vi	Input voltage			-0.5Vcu+0.5	٧		
Vo	Output voltage			-0.5~·Vcc-h0.5	٧		
1	Input protection diade current		V <sub>1</sub> < 0V	-20	29 30		
İıĸ	input protection glode content		V <sub>I</sub> > V <sub>CC</sub>	20	mA		
1200	OK Output parasitic diode current		V <sub>0</sub> < 0 <b>V</b>	-20	35535		
'OK			Vo > Vcc	20	mA.		
lo	Output current per output pin	QA~QH		±35			
····	Catput content per cotput put	SQ <sub>H</sub>		±25	mA		
loc	Supply/GND current		V <sub>CC</sub> , GND	±132	mA		
Pd	Power dissipation	1000000	(Note 2)	500	mW		
Tstg	Storage temperature range			<del>-65</del> ∼+150	°C		

Note 2 : M66312FP :  $T_a = -40 \sim +70 \, \text{C}$  ,  $T_a = 70 \sim 85 \, \text{C}$  are derated at  $-6 \, \text{mW/C}$  .

# RECOMMENDED OPERATING CONDITIONS (Ta=-40~+85°C, unless otherwise noted)

Symbol	Parameter		Unit			
	Farameter	Min	Nom	Max	Unit	
Vaa	Supply voltage		4.5	5	5.5	V
.V <sub>1</sub>	Input voltage		0		Vcc	V
Vo	Output voltage		0		V <sub>CC</sub>	V
Topr	Operating temperature range	3 51 51 600 600 500 500 500 500 500 500 500 500	40	der teter.	十85	$\mathcal{L}$
tr. tf	Input rising and falling time	V <sub>CC</sub> =4.5V	0		500	
n, u	i tiput tising and lating time	0		400	ns	

# ELECTRICAL CHARACTERISTICS (Vcc=4.5~5.5V, unless otherwise noted)

	72, 1946 - ACT (2, 1944)			Limits						
Symbol	Parameter	Test conditions			Ta=257		Ta 40~+85°C		Unit	
				Min	Тур	Max	Min	Max		
V <sub>IH</sub>	High-level input voltage	$V_0 = 0.1V$ , $V_{00} = 0.1V$ $ I_0  = 20\mu A$		0.70× <b>V</b> <sub>00</sub>			0.70×V <sub>oc</sub>	200000000000000000000000000000000000000	٧	
VIL	Low-level input voltage	$V_0 = 0.1V$ , $V_{CC} = 0.1V$ $ I_0  = 20\mu A$				0.30×V <sub>CQ</sub>		0.30×V <sub>CC</sub>	٧	
VoH	High-level output voltage	$V_l = V_{H_1}, V_{IL}$	I <sub>OH</sub> =20 <i>μ</i> A	V <sub>CC</sub> =0.1	OST 18 1-		V <sub>cc</sub> =0.1	11015000	12	
* C 2H	Q <sub>A</sub> ~Q <sub>H</sub>	V <sub>CC</sub> =4.5V	I <sub>OH</sub> = 16mA	3.70*			3.55*		٧	
Voti	High-level output voltage	$V_i = V_{iH}, \ V_{iL}$	I <sub>OH</sub> =-20, A	, V <sub>CC</sub> -0.1			V <sub>CC</sub> −0.1			
* 011	SQ <sub>H</sub>	V <sub>CC</sub> =4.5V	I <sub>OH</sub> =-4mA	4.0			3.9		V	
VoL	Low-level output voltage	$V_{i} = V_{iH}, \ V_{iL}$	i <sub>05</sub> =20μA		100000	0.1	10.000	0.1	v	
• 01	Q <sub>A</sub> ~Q <sub>H</sub>	V <sub>GC</sub> =4.5V	I <sub>OL</sub> =16mA	I	W. 1947 To 2018	0.7*	****	0.85*	٧	
Vol	Low-level output voltage	VI == VIH. VIL	los.=20//A			0.1		0.1		
• 01	SQH	V <sub>CC</sub> =4.5V	IoL= 4 mA			0,4		0.5	V	
l <sub>iH</sub>	High-level input current	V <sub>I</sub> =V <sub>CC</sub> , V <sub>CC</sub> =5.5V				0.1		1.0	μA	
hu	Low-level input current	V <sub>I</sub> =GND, V <sub>CC</sub> =5, 5V				-0.1		1. D	μA	
lozh	Off state high-level output current QATONH	V <sub>I</sub> =V <sub>IH</sub> , V <sub>IL</sub>	Vo=Vcc			1.0	20 10	10.0	//A	
lozu	Off state low-level output current $Q_A \sim Q_H$	V <sub>CC</sub> =5.5∨	Vo=GND			-1,0	on he	-10.D	μΛ	
loc	Quiescent supply current	V <sub>1</sub> =V <sub>CC</sub> , GND, V <sub>CC</sub> =5.5V	25.00 Ave			4.0		40.0	μΑ	

\* : Limits of single PIN operating state



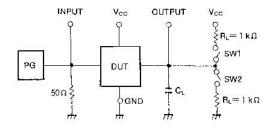
### SWITCHING CHARACTERISTICS (Voo= 5 V)

		1	Limits						
Symbol	Parameter	Test conditions		Ta=25℃	3	Ta=-40~+85℃		Unit	
			Min	Тур	Max	Min	Max	ï	
fmax	Maximum clock frequency	C <sub>L</sub> =50pF	15			12		MHz	
t <sub>PLH</sub>	Low-level to high-level and high-level to low-level				70		88	ns	
t <sub>PHL</sub>	output propagation time CKs-SQ <sub>II</sub>	C <sub>L</sub> =15pF			70		88	ns	
t <sub>PHL</sub>	High-level to low-level output propagation time R-SQ <sub>H</sub>	(Note 3)			60		76	ns	
t <sub>PLH</sub>	Low-level to high-level and high-level to low-level	C <sub>L</sub> =50pF			60	1	76	ns	
teriL	output propagation time CK <sub>L</sub> -Q <sub>A</sub> ~Q <sub>H</sub>	(Note 3)			60		76	ns	
tpLZ	Output disable time from low-level and high-fevel	C <sub>L</sub> =5pF			50		64	пз	
1 <sub>PHZ</sub>	OÊ-Q <sub>A</sub> ~Q <sub>H</sub>	(Note 3)			50		64	ns	
t <sub>PZL</sub>	Output enable time to low-level and high-level	C <sub>L</sub> =50pF		500-50 0000000000	56	1	70	ns	
t <sub>PZH</sub>	OE-Q <sub>A</sub> ~Q <sub>H</sub>	(Note 3)	l	2017 100000	56		70	ns	

# TIMING REQUIREMENTS (Vac= 5 V)

Symbol	į		Limits						
	Parameter	Test conditions	Ta=25℃			Ta=-40	Unit		
			Min	Тур	Max	Min	Max		
tw	CK <sub>s</sub> , CK <sub>L</sub> , R pulse width		32			40		лѕ	
t <sub>su</sub>	A setup time with respect to CK <sub>S</sub>		40			50		ns	
tsu	CKs setup time with respect to CKL		40			50		ns	
th	A hold time with respect to CKs		10			10		ns	
trec .	R recovery time with respect to CKs		20	• • • • • • • • • • • • • • • • • • • •		26		пв	

Note 3 : Test Circult



Item	SW1	SW2		
t <sub>PLH</sub> , t <sub>PHL</sub>	OPEN	OPEN		
t <sub>PLZ</sub>	CLOSE	OPEN		
t <sub>PHZ</sub>	OPEN	CLOSE		
t <sub>PZL</sub>	CLOSE	OPEN		
tezn	OPEN	CLOSE		

- (1) The pulse generator (PG) has the following characteristics (10% $\sim$ 90%) : tr =6ns, tr=6ns
- $\langle 2 \rangle$  . The capacitance  $C_L$  includes stray wiring capacitance and the probe input capacitance.

### **TIMING DIAGRAM**

